

MOSFETs Silicon N-channel MOS (U-MOSVIII)

TPN2R203NC

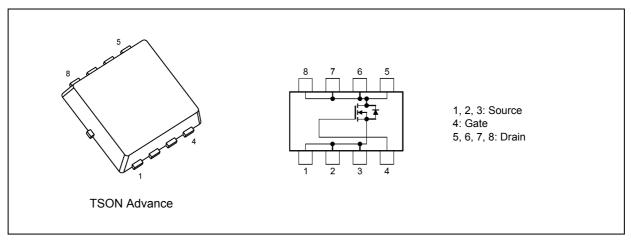
1. Applications

· Power Management Switches

2. Features

- (1) Low drain-source on-resistance: $R_{DS(ON)} = 1.8 \text{ m}\Omega$ (typ.) ($V_{GS} = 10 \text{ V}$)
- (2) Low leakage current: $I_{DSS} = 10 \mu A \text{ (max) (V}_{DS} = 30 \text{ V)}$
- (3) Enhancement mode: V_{th} = 1.3 to 2.3 V (V_{DS} = 10 V, I_{D} = 0.5 mA)

3. Packaging and Internal Circuit



4. Absolute Maximum Ratings (Note) (Ta = 25 °C unless otherwise specified)

Characterist	tics		Symbol	Rating	Unit
Drain-source voltage			V_{DSS}	30	V
Gate-source voltage			V _{GSS}	±20	V
Drain current (DC)	(Silicon limit)	(Note 1), (Note 2)	I _D	100	Α
Drain current (DC)	(T _c = 25 °C)	(Note 1)	I _D	45	Α
Drain current (pulsed)	(t = 1 ms)	(Note 1)	I _{DP}	200	Α
Power dissipation	(T _c = 25 °C)		P _D	42	W
Power dissipation	(t = 10 s)	(Note 3)	P_{D}	1.9	W
Power dissipation	(t = 10 s)	(Note 4)	P_{D}	0.7	W
Single-pulse avalanche energy		(Note 5)	E _{AS}	126	mJ
Avalanche current			I _{AR}	45	Α
Channel temperature			T _{ch}	150	°C
Storage temperature			T _{stg}	-55 to 150	°C

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Start of commercial production



5. Thermal Characteristics

Characteristics	Symbol	Max	Unit		
Channel-to-case thermal resistance	(T _c = 25 °C)		R _{th(ch-c)}	2.97	°C/W
Channel-to-ambient thermal resistance	(t = 10 s)	(Note 3)	R _{th(ch-a)}	65.7	°C/W
Channel-to-ambient thermal resistance	(t = 10 s)	(Note 4)	R _{th(ch-a)}	178	°C/W

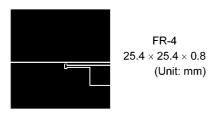
Note 1: Ensure that the channel temperature does not exceed 150 °C.

Note 2: Limited by silicon chip capability.

Note 3: Device mounted on a glass-epoxy board (a), Figure 5.1

Note 4: Device mounted on a glass-epoxy board (b), Figure 5.2

Note 5: V_{DD} = 24 V, T_{ch} = 25 °C (initial), L = 0.048 mH, I_{AR} = 45 A



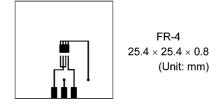


Fig. 5.1 Device Mounted on a Glass-Epoxy Board (a)

Fig. 5.2 Device Mounted on a Glass-Epoxy Board (b)

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.



6. Electrical Characteristics

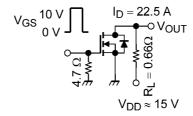
6.1. Static Characteristics ($T_a = 25$ °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current	I _{GSS}	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$	_	_	±0.1	μА
Drain cut-off current	I _{DSS}	V _{DS} = 30 V, V _{GS} = 0 V			10	μА
Drain-source breakdown voltage	V _{(BR)DSS}	$I_D = 10 \text{ mA}, V_{GS} = 0 \text{ V}$	30			V
Drain-source breakdown voltage (Note 6)	V _{(BR)DSX}	$I_D = 10 \text{ mA}, V_{GS} = -20 \text{ V}$	15			V
Gate threshold voltage	V_{th}	$V_{DS} = 10 \text{ V}, I_D = 0.5 \text{ mA}$	1.3	_	2.3	V
Drain-source on-resistance	R _{DS(ON)}	V _{GS} = 4.5 V, I _D = 22.5 A	_	2.8	3.6	mΩ
Drain-source on-resistance	R _{DS(ON)}	V _{GS} = 10 V, I _D = 22.5 A		1.8	2.2	mΩ

Note 6: If a reverse bias is applied between gate and source, this device enters $V_{(BR)DSX}$ mode. Note that the drain-source breakdown voltage is lowered in this mode.

6.2. Dynamic Characteristics (T_a = 25 °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Input capacitance	C _{iss}	V _{DS} = 15 V, V _{GS} = 0 V, f = 1 MHz	_	2230	_	pF
Reverse transfer capacitance	C _{rss}		-	160	_	pF
Output capacitance	C _{oss}		_	650	_	pF
Switching time (rise time)	t _r	See Fig. 6.2.1	_	9	_	ns
Switching time (turn-on time)	t _{on}		_	14	_	ns
Switching time (fall time)	t _f		_	24	_	ns
Switching time (turn-off time)	t _{off}		1	68	_	ns



Duty \leq 1%, $t_{W}=$ 10 μs

Fig. 6.2.1 Switching Time Test Circuit

6.3. Gate Charge Characteristics (T_a = 25 °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Total gate charge (gate-source plus gate-drain)	, ,	$V_{DD} \approx 15 \text{ V}, V_{GS} = 10 \text{ V},$	_	34	_	nC
Gate-source charge 1	Q _{gs1}	I _D = 45 A	_	8	_	nC
Gate-drain charge	Q_{gd}			6		nC

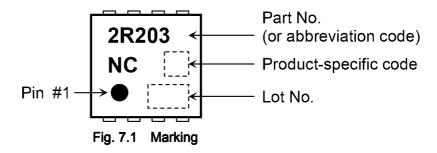
6.4. Source-Drain Characteristics (T_a = 25 °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Reverse drain current (pulsed) (1 ms) (Note 7)	I _{DRP}	_	_	_	200	Α
Diode forward voltage	V_{DSF}	I _{DR} = 45 A, V _{GS} = 0 V			-1.2	V

Note 7: Ensure that the channel temperature does not exceed 150 °C.



7. Marking



Rev.3.0



8. Characteristics Curves (Note)

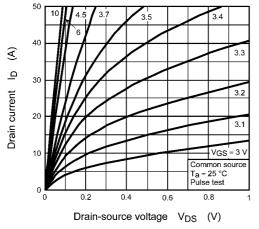
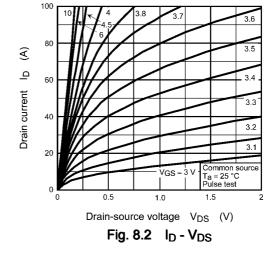


Fig. 8.1 I_D - V_{DS}



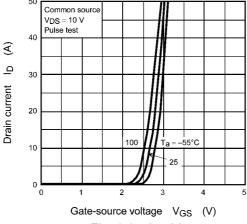


Fig. 8.3 I_D - V_{GS}

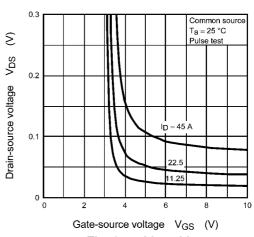


Fig. 8.4 V_{DS} - V_{GS}

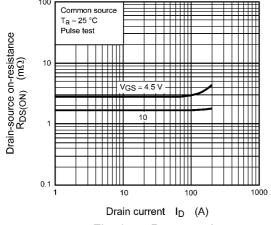


Fig. 8.5 R_{DS(ON)} - I_D

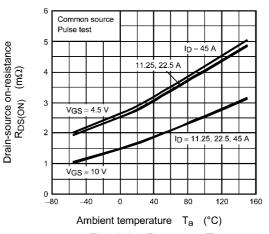


Fig. 8.6 R_{DS(ON)} - T_a



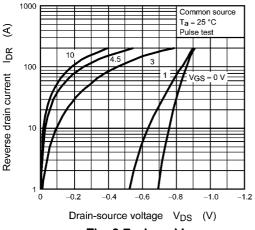
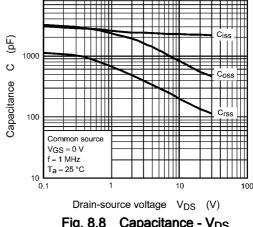


Fig. 8.7 I_{DR} - V_{DS}



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Fig. 8.8 Capacitance - V_{DS}

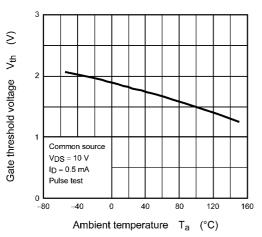


Fig. 8.9 V_{th} - T_a

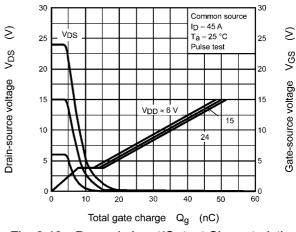


Fig. 8.10 Dynamic Input/Output Characteristics

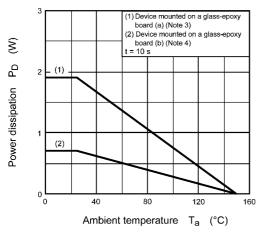


Fig. 8.11 PD - Ta (Guaranteed Maximum)

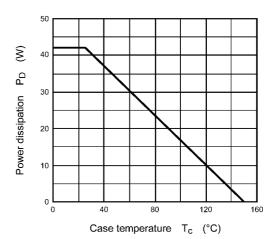


Fig. 8.12 P_D - T_c (Guaranteed Maximum)

Rev.3.0



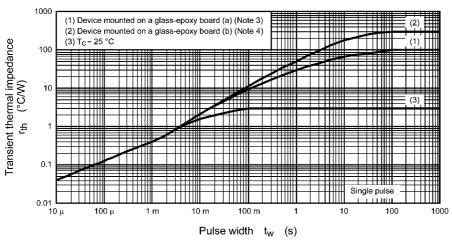


Fig. 8.13 r_{th} - t_w (Guaranteed Maximum)

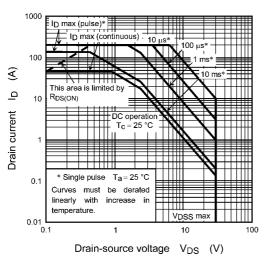


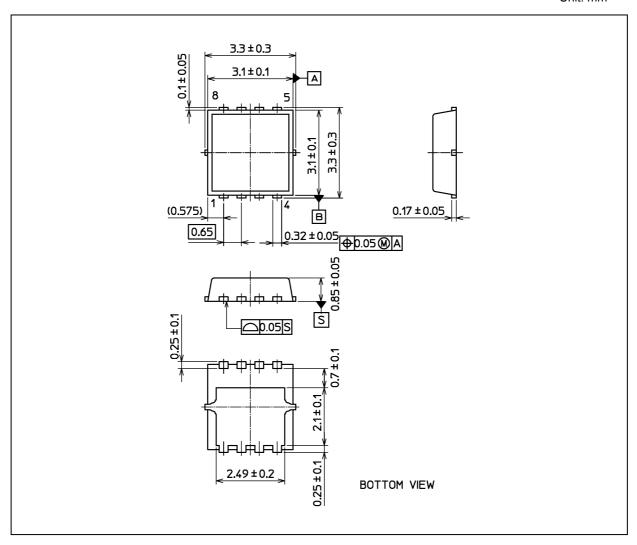
Fig. 8.14 Safe Operating Area (Guaranteed Maximum)

Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.



Package Dimensions

Unit: mm



Weight: 0.029 g (typ.)

Package Name(s)
TOSHIBA: 2-3X1S
Nickname: TSON Advance



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